



ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor article comprises steps of forming a diffusion region at least on the surface of one of the sides of a silicon substrate by diffusing an element capable of controlling the conduction type, forming a porous silicon layer in a region including the diffusion region, preparing a first substrate by forming a nonporous semiconductor layer on the porous silicon layer, bonding the first substrate and a second substrate together to produce a multilayer structure with the nonporous semiconductor layer located inside, splitting the multilayer structure along the porous silicon layer but not along the diffusion region and removing the porous silicon layer remaining on the split second substrate.

This Sheet Has Been Replaced

